

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
9 June 2005 (09.06.2005)

PCT

(10) International Publication Number
WO 2005/052892 A1

(51) International Patent Classification⁷: **G09F 9/00**,
H05B 33/10, G02F 1/1333

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(21) International Application Number:
PCT/JP2004/017522

(22) International Filing Date:
18 November 2004 (18.11.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-399978 28 November 2003 (28.11.2003) JP

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

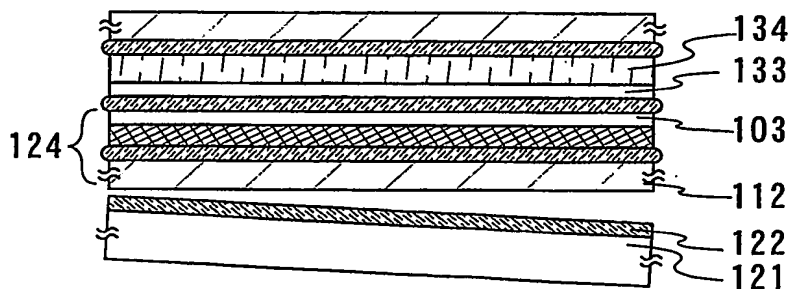
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LU, MC, NL, PL, PT, RO, SE,
SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: METHOD OF MANUFACTURING DISPLAY DEVICE



(57) Abstract: To provide a method of
manufacturing a display device having
an excellent impact resistance property
with high yield, in particular, a method
of manufacturing a display device
having an optical film that is formed
using a plastic substrate. The method of
manufacturing a display device includes
the steps of: sequentially forming a
metal film, an oxide film, and an optical
filter on a first substrate; separating
layers including the optical filter from
the first substrate; attaching layers
including the optical filter to a second

substrate; forming a layer including a pixel on a surface of a third substrate; attaching the layer including the pixel to a fourth
substrate; and attaching layers including the optical filter to another surface of the third substrate.